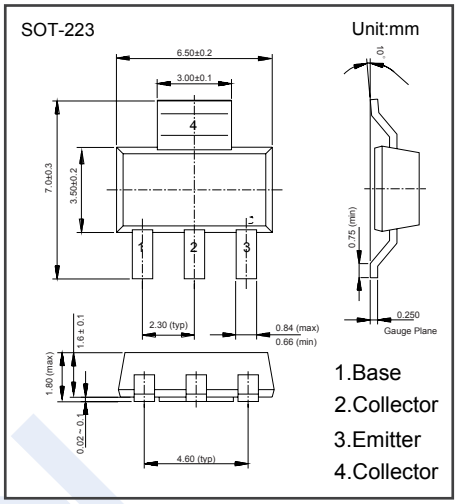
PNP Transistors

FZT958 (KZT958)



■ Features

- Collector Current Capability I_C=-0.5A
- Collector Emitter Voltage V_{CEO}=-400V

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-400	V
Collector - Emitter Voltage	V_{CEO}	-400	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-0.5	A
Collector Current - Pulse	I_{CP}	-1.5	
Collector Power Dissipation	P_C	3	W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA， I_E=0	-400			V
Collector-emitter breakdown voltage	V_{CER}	I_C= -100 μA, RB≤1KΩ	-400			
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA， I_B=0	-400			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100μA， I_C=0	-6			
Collector-base cut-off current	I_{CBO}	V_{CB}= -300 V , I_E=0			-50	nA
		V_{CB}= -300 V , I_E=0 , Ta = 100℃			-1	uA
Collector cut-off current R≤1KΩ	I_{CER}	V_{CE}= -300 V , I_E=0			-50	nA
		V_{CE}= -300 V , I_E=0 , Ta = 100℃			-1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -6V , I_C=0			-10	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B=-1mA			-150	mV
		I_C=-100 mA, I_B=-10mA			-200	
		I_C=-500 mA, I_B=-100mA			-400	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-500 mA, I_B=-100mA			-0.95	V
Base - emitter turn-on voltage	$V_{BE(on)}$	V_{CE}= -10V, I_C= -0.5A			-0.84	
DC current gain	h_{FE}	V_{CE}= -10V, I_C= -10mA	100			
		V_{CE}= -10V, I_C= -500mA	100		300	
		V_{CE}= -10V, I_C= -1A	10			
Turn-on time	t_{on}	I_C=-500mA, I_{B1}=-50mA I_{B2}=50mA, V_{CC}=-100V		104		ns
Turn-off time	t_{off}			2400		
Collector output capacitance	C_{ob}	V_{CB}= -20V,f=1MHz		19		pF
Transition frequency	f_T	V_{CE}= -10V, I_C= -100mA,f=50MHz		85		MHz

Note.Measured under pulsed conditions. Pulse width=300us. Duty cycle ≤2%

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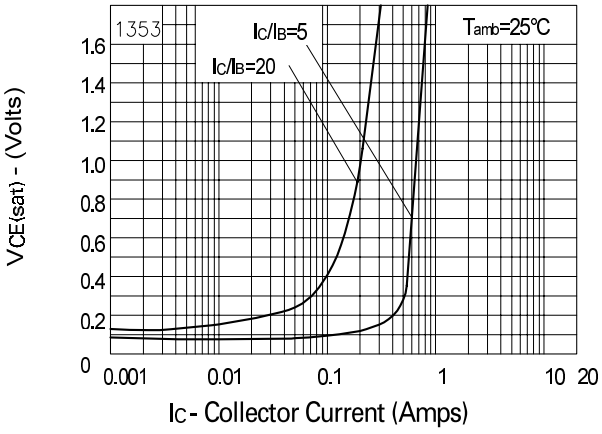
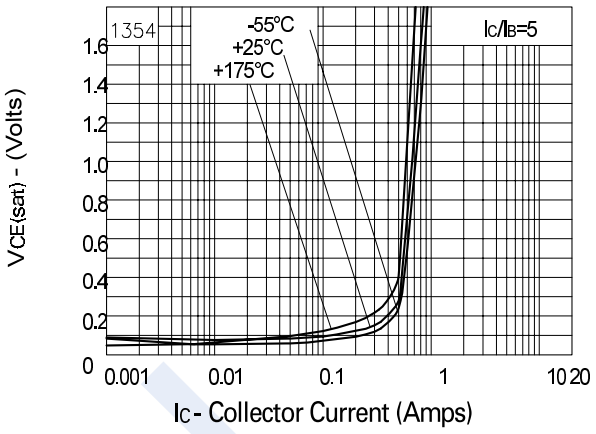
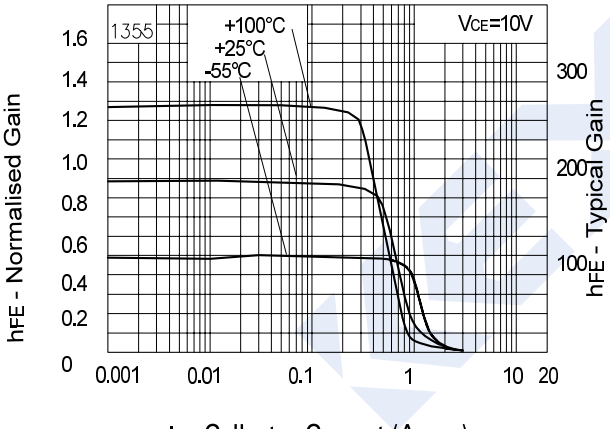
■ Typical Characterisitics



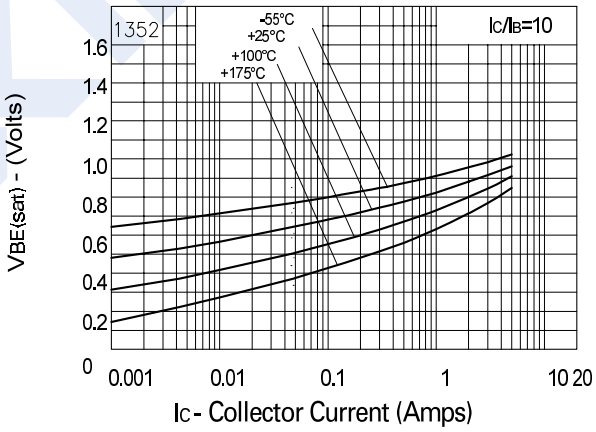
VCE(sat) v IC



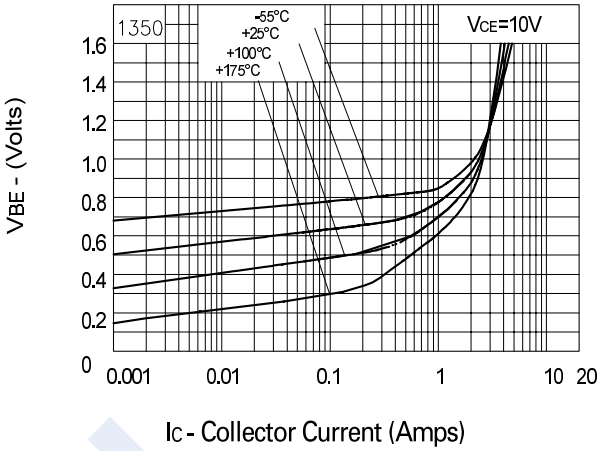
VCE(sat) v IC



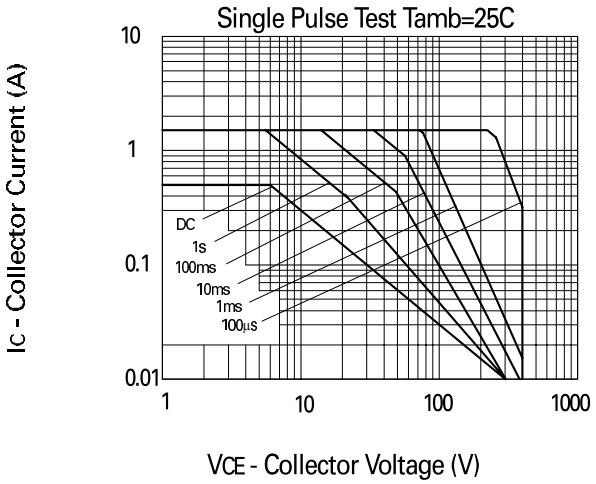
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area